

# WS3A040065K

## Silicon Carbide Schottky Diode

$V_{RRM}$	=	650	V
I <sub>F</sub> ( T <sub>C</sub> ≤135°C)	=	52	A**
Q <sub>C</sub>	=	80	nC**

#### **Features**

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on V<sub>F</sub>
- Temperature-independent Switching
- 175°C Operating Junction Temperature

### **Benefits**

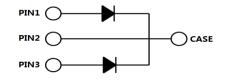
- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

## **Applications**

- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

### **Package**



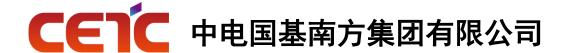


Part Number	Package	Marking
WS3A040065K	TO-247-3	WS3A040065K

## **Maximum Ratings**

Symbol	Parameter	Value	Unit	Test Conditions	Note
$V_{RRM}$	Repetitive Peak Reverse Voltage	650	V	T <sub>C</sub> = 25°C	
$V_{RSM}$	Surge Peak Reverse Voltage	650	٧	$T_C = 25^{\circ}C$	
V <sub>R</sub>	DC Blocking Voltage	650	V	T <sub>C</sub> = 25°C	
I <sub>F</sub>	Forward Current (Per leg/Device)	57/114 26/52 20/40	А	T <sub>C</sub> ≤ 25°C T <sub>C</sub> ≤ 135°C T <sub>C</sub> ≤ 148°C	
I <sub>FSM</sub>	Non-Repetitive Forward Surge Current	170*	Α	$T_C = 25^{\circ}C$ , $t_p = 8.3$ ms, Half Sine Wave	
P <sub>tot</sub>	Power Dissipation (Per leg/Device)	187/ 374	W	$T_C = 25^{\circ}C$	Fig.3
Tc	Maximum Case Temperature	148	°C		
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature	-55 to 175	°C		
	TO-247 Mounting Torque	1	Nm	M3 Screw	

<sup>\*</sup>Per Leg, \*\*Per Device



## **Electrical Characteristics (Per Leg)**

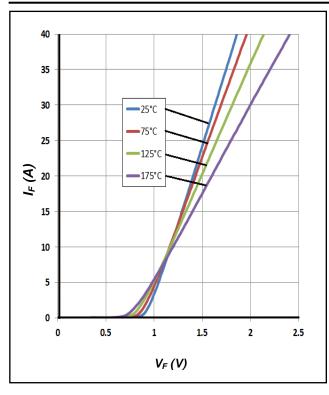
Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note	
V <sub>F</sub>	Forward Voltage	1.4	1.65	V	I <sub>F</sub> = 20A, T <sub>J</sub> = 25°C	F: ~ 4	
		1.75		I <sub>F</sub> = 20A, T <sub>J</sub> = 175°C	Fig.1		
	Davis Comment	1	20		V <sub>R</sub> = 650V, T <sub>J</sub> = 25°C	F: 0	
I <sub>R</sub>	Reverse Current	5	5 100	μA	V <sub>R</sub> = 650V, T <sub>J</sub> = 175°C	Fig.2	
		1190			$V_R = 0V, T_J = 25^{\circ}C, f = 1MHz$		
С	Total Capacitance	115	/	pF	$V_R = 200V, T_J = 25^{\circ}C, f = 1MHz$	Fig.5	
			96			$V_R = 400V, T_J = 25^{\circ}C, f = 1MHz$	
Qc	Total Capacitive Charge		,		$V_R = 650V, I_F = 20A$	F: . 4	
		Total Capacitive Charge 40	/	nC	di/dt = 200A/μs, T <sub>J</sub> = 25°C	Fig.4	

### **Thermal Characteristics**

Symbol	Parameter	Тур.	Unit	Note
R <sub>0</sub> JC	R <sub>eJC</sub> Thermal Resistance from Junction to Case		°C/W	Fig.6
R <sub>θJA</sub> Thermal Resistance from Junction to Ambient		80	°C/W	
T <sub>sold</sub> Soldering Temperature		260	°C	

<sup>\*</sup>Per Leg, \*\*Per Device

## **Typical Performance (Per Leg)**



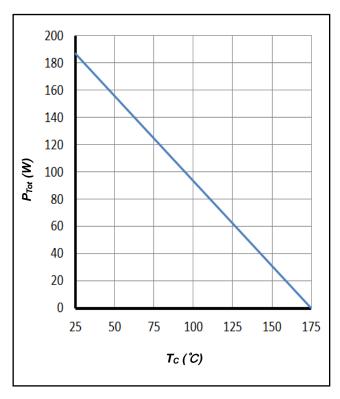
100 80 -25°C -75°C -125°C -175°C 20 20 20 20 V<sub>R</sub> (V)

Figure 1. Forward Characteristics

Figure 2. Reverse Characteristics

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## **Typical Performance (Per Leg)**



5  $V_R(V)$ 

Figure 3. Power Derating

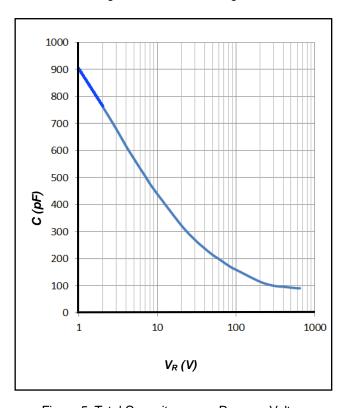


Figure 5. Total Capacitance vs. Reverse Voltage

Figure 4. Total Capacitive Charge vs. Reverse Voltage

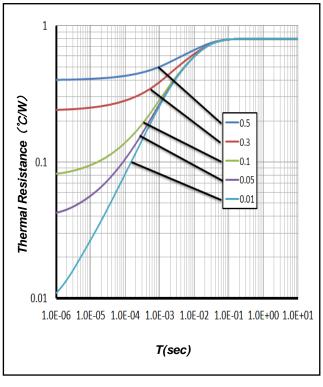
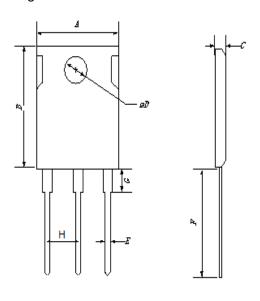


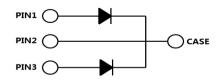
Figure 6. Transient Thermal Impedance

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## **Package Dimensions**

Package TO-247-3

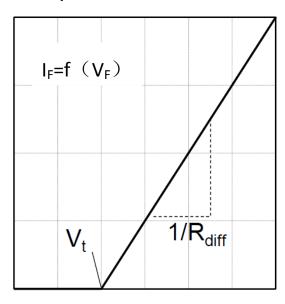




Symbol	Min. (mm)	Typ. (mm)	Max. (mm)
Α	14.18	15.75	17.33
В	18.45	20.5	22.55
С	4.50	5.00	5.50
D	3.15	3.50	3.85
E	1.08	1.20	1.32
F	18.27	20.30	22.33
G	4.21	4.68	5.15
Н	4.91	5.46	6.01

### Simplified Diode Model (Per Leg)

### **Equivalent IV Curve for Model**



### **Mathematical Equation**

$$V_F = V_t + I_F \times R_{diff}$$

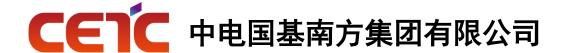
$$\begin{aligned} V_t &= -0.0011 \times T_j + 0.99 \text{ [V]} \\ R_{diff} &= 3.6 \times 10^{-7} \times T_j^2 + 5.2 \times 10^{-5} \times T_j + 0.020 \text{ [}\Omega\text{]} \end{aligned}$$

### Note:

Tj = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C  $I_{\text{F}}$ = Forward Current

i a de la desira

Less than 40A



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